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	APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
	09/974,582	10/09/2001	Ming-Chung Liang	JCLA7521	8293
	5	7590 05/21/2003			
	J.C. Patents, 1	Inc.		EXAMI	NER
	Suite 250 4 Venture			MACKEY, TERRENCE M	
	Irvine, CA 92	2618		ART UNIT	PAPER NUMBER
				1765	.7
				DATE MAILED: 05/21/2003	_)

Please find below and/or attached an Office communication concerning this application or proceeding.

			AS-3			
	Application No.	Applicant(s)	, , ,			
	09/974,582	LIANG, MING-CHU	LIANG, MING-CHUNG			
Office Action Summary	Examiner	Art Unit				
	Terrence Mackey	1765				
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet v	vith the correspondence add	ress			
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl - If NO period for reply is specified above, the maximum statutory period of the period of the period for reply within the set or extended period for reply will, by statute - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). Status	136(a). In no event, however, may a ly within the statutory minimum of th will apply and will expire SIX (6) MC a, cause the application to become A	reply be timely filed irty (30) days will be considered timely. NTHS from the mailing date of this com BANDONED (35 U.S.C. § 133).	nmunication.			
1) Responsive to communication(s) filed on	·					
2a) This action is FINAL . 2b) ⊠ Th	nis action is non-final.					
3) Since this application is in condition for allows closed in accordance with the practice under Disposition of Claims			merits is			
4) Claim(s) $1 - 22$ is/are pending in the application	on.					
4a) Of the above claim(s) is/are withdra	wn from consideration.					
5) Claim(s) is/are allowed. 6) Claim(s) <u>1 - 22</u> is/are rejected.						
8) Claim(s) are subject to restriction and/o	or election requirement.					
Application Papers						
9)⊡ The specification is objected to by the Examine	er.					
10) ☐ The drawing(s) filed on is/are: a) ☐ acce	pted or b) ☐ objected to by	the Examiner.				
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
11)☐ The proposed drawing correction filed on		disapproved by the Examiner	Г.			
If approved, corrected drawings are required in re	. •					
12) The oath or declaration is objected to by the Ex	caminer.					
Priority under 35 U.S.C. §§ 119 and 120						
13) Acknowledgment is made of a claim for foreign	n priority under 35 U.S.C	§ 119(a)-(d) or (f).				
a)⊠ All b)□ Some * c)□ None of: —						
1. Certified copies of the priority document	1. Certified copies of the priority documents have been received.					
2. Certified copies of the priority documents have been received in Application No						
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
	Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).					
a) The translation of the foreign language pro	a) The translation of the foreign language provisional application has been received. Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.					
Attachment(s)	as phoney under 00 0.0.0	33 TEV WHO OF TET.				
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice o	v Summary (PTO-413) Paper No(s f Informal Patent Application (PTO				

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DETAILED ACTION

Specification

The disclosure is objected to because of the following informalities: etching rates on pages 6 and 7 are lacking units of measure and the etching uniformity parameter disclosed on page 7 is inadequately described.

Appropriate correction is required.

Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claim 9 recites the limitation "partially fluoro-substituted alkane gas" in line 1.

There is insufficient antecedent basis for this limitation in the claim.

Claim 15 recites the limitation "a ratio of CHF₃ to CF₄" in line 1. There is insufficient antecedent basis for this limitation in the claim.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

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Claims 1 – 22 are rejected under 35 U.S.C. 102(a) as being anticipated by Arleo et al. (5,176,790). Applicant claims a plasma etching gas and process for etching a silicon oxide layer using the etching gas. The etching gas consists of a fluoroalkane gas and nitrogen gas. The nitrogen gas has a flow rate of about 1 sccm to about 50 sccm. The fluoroalkane gas may comprise a mixture of a partially fluoro-substituted alkane gas (CH_3F , CHF_3 , and CH_2F_2) and a fully fluoro-substituted alkane gas (CF_4 , C_2F_6 , C_3F_8 , and C_4F_8) in a ratio of about 3/1 to 15/1. The etching gas may further comprise argon gas having a flow rate of about 50 sccm to about 150 sccm.

Arleo et al. disclose a process for plasma etching vias in a silicon oxide layer on an integrated circuit substrate by flowing an etchant gas composition comprising about 3 sccm of N₂, about 25 sccm of CHF₃, about 5 sccm of CF₄, and about 75 sccm of argon (column 7, lines 4-8).

Conclusion

Remaining references cited of interest to show the state of the art.

No claim is allowed.

Papers relating to this application may be submitted to Technology Sector 1700 by facsimile transmission. Papers should be faxed to Crystal Plaza 3, Art Unit 1765, using fax number (703) 305-6357. All Technology Section 1700 fax machines are available to receive transmissions 24 hrs/day, 7 days/wk. Please note that the faxing of such papers must conform to the Notice published in the Official Gazette, 1096 OG 30, (November 15, 1989).

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Any inquiry concerning this communication or earlier communications from the Examiner should be directed to Terrence Mackey whose telephone number is (703) 305-5504. The Examiner can normally be reached Monday - Friday from 7:00 AM – 4:30 PM.

If attempts to reach the Examiner by telephone are unsuccessful, the examiner's supervisor, Ben Uteck, can be reached at (703) 308-3836.

Any inquiry of a general nature or relating to the status of this application should be directed to the receptionist whose telephone number is (703) 308-0661.

MMT

May 13, 2003

PRIMARY EXAMINED